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TABLE OF CONTENTS

Greetings from the General Chair of Radio & Wireless Week 2025 i

Technical Program Chair's Welcome Message ii

RWW 2025 Steering Committee ii

Exhibitors & Sponsors iii

Author Index 86

Session Mo1C : K-/Ka-Band Low-Noise Amplifiers and Optical Receiver

Mo1C-1
CMOS LNA and VGA for K-Band LEO SATCOM Receiver Using Body-to-Source Floating Technique 1
Yo-Sheng Lin, *Jin-Fa Chang*, *Yu-Hao Zhuang*

Mo1C-2
A Two-Stage Ka-Band Transformer-Feedback Low-Noise Amplifier in 90-nm CMOS Technology 4
Yu-Chia Su, *Kuei-Hao Huang*, *Yi-Fu Chen*, *Po-Lei Lee*, *Hong-Yeh Chang*

Mo1C-3
Low Power K- and Ka- Wideband LNA Design in 22nm FD-SOI Using Transformer-Tuned Input 8
Martin Rack, *Sidina Wane*, *Damienne Bajon*, *Jean-Pierre Raskin*, *Dimitri Lederer*

Mo1C-4
44GHz Bandwidth Optical Receiver Monolithically Integrated in a SiGe ePIC BiCMOS Technology 12
Festim Iseini, *Andrea Malignaggi*, *Nicola Pelagalli*, *Anna Peczek*, *Corrado Carta*, *Gerhard Kahmen*

Session Mo2C : RF/mm-Wave Front-Ends and Phased Arrays

Mo2C-1
A 5.1–10.5GHz SiGe BiCMOS Power Amplifier for 6G NR with 29dBm P_{SAT} and 40.1% PAE 15
Davide Pecile, *Stefan Kokorovic*, *Alberto Gambarucci*, *Andrea Bevilacqua*

Mo2C-2
A High-Gain 240–325-GHz Power Amplifier for IEEE 802.15.3d Applications in an Advanced BiCMOS Technology 19
Ahmed Gadallah, *Andrea Malignaggi*, *Batuhan Sutbas*, *Holger Rücker*, *Dietmar Kissinger*, *Mohamed Hussein Eissa*

Mo2C-3
A V-Band VSPS Using Deep-Saturated SiGe HBTs with 0.34dB Amplitude and 0.7° Phase Errors 23
Batuhan Sutbas, *Mohamed Hussein Eissa*, *Gerhard Kahmen*

Mo2C-4
90–100GHz 6-Bit Blixer-Based Active Phase Shifter in SiGe BiCMOS 26
Kateryna Smirnova, *Mark van der Heijden*, *Domine Leenaerts*, *Ahmet Çağrı Ulusoy*

Mo2C-5
A Fully-Integrated Four-Channel Phased Array D-Band Transceiver Achieving 10GBit/s at 10m 30
Christoph Herold, *Alper Karakuzulu*, *Andrea Malignaggi*, *Matthias Scheide*, *Nebojsa Maletic*, *Karthik Krishnegowda*, *Corrado Carta*

Session Mo3C: Signal Generation and Frequency Conversion

Mo3C-1
A Stacked Class-F VCO in 45nm SOI CMOS 33
Sutton Hathorn, Saeed Mohammadi

Mo3C-2
>7dBm, 89.8–97.2GHz Colpitts-Clapp VCO Using Forward-Biased Diodes in 0.25μm InP-HBT 36
Satoshi Kawahara, Tsutomu Takeya, Teruo Jyo, Hitoshi Wakita, Munehiko Nagatani, Miwa Mutoh, Yuta Shiratori, Hiroyuki Takahashi

Mo3C-3
A D-Band 6.8GHz Lock Range 5th Sub-Harmonic Injection-Locked Oscillator in 22nm FDSOI 39
Andre Engelmann, Florian Probst, Philip Hetterle, Kai Scheller, Albert-Marcel Schrotz, Robert Weigel

Mo3C-4
A 7mW 22GHz Frequency Divider Chain by 2048 Using CML, TSPC and CMOS Logic in 22FDX 42
Tetiana Baluta, Alexander Meyer, Adilet Dossanov, Yerzhan Kudabay, Liubov Bakhchova, Vadim Issakov

Session Tu1C: Devices, Technology and Integration

Tu1C-1
Application of Device-Degradation Modeling to SiGe-LNA Analysis 46
Taeyeong Kim, Jongho Lee, Junhwa Jeong, Michael A. Oakley, John D. Cressler, Ickhyun Song

Tu1C-2
Characterization of HBT-Based Avalanche Noise Sources Using Standard Test Structures for Measurement of Transistor Scattering Parameters 50
Ethan Bernardini, Giacomo Schiavolini, Giulia Orecchini, Gunter Fischer, Corrado Carta, Federico Alimenti

Tu1C-3
Robust Measurement and De-Embedding Techniques of Si/SiGe HBT Devices up to 500GHz 53
Philippine Billy, Jojo Varghese, Magali De Matos, Didier Celi, Nicolas Derrier, Alexis Gauthier, Pascal Chevalier, Thomas Zimmer, Sebastien Fregonese

Tu1C-4
Field Effect Strategy to Enhance RF Performance of High-Resistivity Silicon Substrates 57
Massinissa Nabet, Martin Rack, Yiyi Yan, Kumar Prasannajit Pradhan, Jean-Pierre Raskin

Session IF1 : Interactive Forum

IF-8
A Compact 245–310GHz Balun in 130-nm SiGe BiCMOS Technology 61
Aniello Franzese, Batuhan Sutbas, Volkan Erturk, Thomas Mausolf, David Bierbüsse, Renato Negra, Ehsan Shokrolahzade, Marco Spirito, Corrado Carta

IF-9
A 268GHz LNA for Sub-THz Applications in a 90nm SiGe:C Technology 64
Hakan Papurcu, Melika Dedovic, Florian Vogelsang, Klaus Aufinger, Nils Pohl

IF-10
A 0.37 THz Subharmonic Downconverting IQ Mixer in a 90nm SiGe:C BiCMOS Technology with High Image Rejection Ratio 68
Melika Dedovic, Tobias T. Braun, Jan Schoepfel, Jonathan Bott, Florian Vogelsang, Hakan Papurcu, David Starke, Klaus Aufinger, Nils Pohl

IF-11
A 40–58GHz Differential Three-Push Frequency Tripler in a 90-nm SiGe BiCMOS Technology 72
Muhammed Ali Yildirim, Justin Romstadt, Pascal Stadler, Tobias Welling, Klaus Aufinger, Nils Pohl

IF-12
Voltage-Controlled-Oscillator with Hybrid Tail Inductor and Source-Degenerated Inductor 76
Sheng-Lyang Jang, Erica Lin, Chun-Ren Chen, Wen-Cheng Lai

IF-13
Integration of Lateral Si/SiGe HBTs on Advanced FD-SOI Technology: Process Development and Challenges 79
Philippine Billy, Soumya Ranjan Panda, Nicolas Guitard, Olivier Weber, Alexis Gauthier, Pascal Chevalier, Thomas Zimmer, Sebastien Fregonese

IF-14
Analysis of Calibration and De-Embedding for On-Wafer Characterization up to 170GHz in 22-nm FDSOI CMOS Technology 83
Quang Huy Le, Kaiwen Feng, Thomas Kämpfe